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STAT	EMENT BY se as many sheets	APPL	ICANT	176	plicant(s	CERTIFICATION		Chi-Chun Chen et al. 2822	E.		E
				Ę	aminer N	ame.		Thomas, Toniae M.		MADELLE	
SHEET	1	OF	1	JAI	torney/Do	cket Numb	er,	2002-0066 / 24061.461			

			U. S. PATENT DO	
Examiner's	Cite :	Document Number	Publication Date?	Name of Patentee or Applicant of Cited Document
\mathcal{N}	AA	-5960289 -	-09-28-19 99	Touistal: Already considered
	^ AB	-6030802	-02-20-200 0	Kepler 11 3 11
	AC	-603722 4	93-14-2000	Buller et al.
\mathbb{V}	AD	-611084 2	98-29-2000 -	Okunno ot al.
IMI	AE	6121091	09-19-2000	Wang
	AF	-6262455	07-17-2001	Luize et al
\searrow	AG	6294421*	- 09-25-2001	Genzalez etal. Patent Unavailable
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			-	

	FOREIGN PATENT DOCUMENTS							
Examiner's Initials	Cite No:	Foreign Patent 24 7	Publication Date	Ratentee or Applicant of (Document	Cited Translation			

		OTHER PRIOR ART
Examiner's	Cite.	/ Include name of the author (in CAPITAL LETTERS) (title of the article title of the item date; page(s); volume
	AH	G. LUCOVSKY et al., "Formation of thin film dielectrics by remove plasma-enhanced chemical-vapor deposition (remote PECVD)", Applied Surface Science, Volume 39, Issue 1-4, October 1989, Pages 33-36.
SMI	Al	STANLEY WOLF et al., "Silicon Processing For The VLSI Era, Volume 1: Process Technology", Lattice Press, Sunset Beach, CA, 3 pages
Jm1	AJ	HOWARD CHIH-HAO WANG et al., "Hot Carrier Reliability Improvement by Utilizing Phosphorus Transient Enhanced Diffusion for Input/Output Devices of Deep Submicron CMOS Technology", IEEE Electronic Device Letters, Vol. 21, No. 12, December 2000, 2 pages
IM1	AK	HOWARD CHIH-HAO WANG et al., "Arsenic/Phosphorus LDD Optimization by Taking Advantage of Phosphorus Transient Enhanced Diffusion for High Voltage Input/Output CMOS Devices", IEEE Transactions on Electron Devices, Volume 49, No. 1, January 2002, 5 pages.